

General Description

The MY003BBNE3 is the highest performance trench N-ch MOSFETS with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the small power switching and load switch applications.

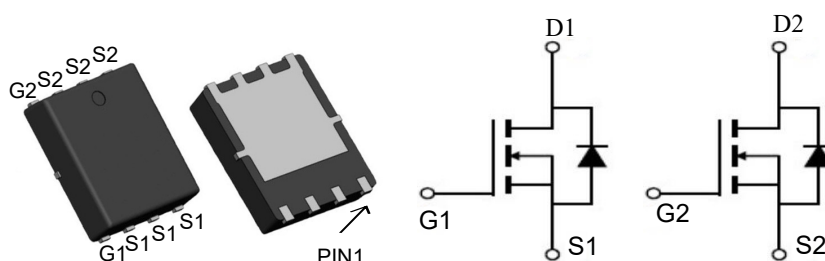


Features

V_{DSS}	20	V
I_D	80	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	5	m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	9	m Ω

Application

- Battery protection
- Load switch
- Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY003BBNE3	PDFN3*3-8	3350	5000

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_{D@T_C=25^\circ\text{C}}$	Continuous Drain Current, V_{GS} @ 4.5V ¹	80	A
$I_{D@T_C=100^\circ\text{C}}$	Continuous Drain Current, V_{GS} @ 4.5V ¹	50	A
$I_{D@T_A=25^\circ\text{C}}$	Continuous Drain Current, V_{GS} @ 4.5V ¹	30	A
$I_{D@T_A=70^\circ\text{C}}$	Continuous Drain Current, V_{GS} @ 4.5V ¹	15	A
I_{DM}	Pulsed Drain Current ²	100	A
$P_{D@T_C=25^\circ\text{C}}$	Total Power Dissipation ¹	31	W
$P_{D@T_A=25^\circ\text{C}}$	Total Power Dissipation ¹	3.6	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	35	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	4	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	20	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=4.5V$, $I_D=3A$	---	1.5	2.5	m Ω
		$V_{GS}=3.9V$, $I_D=3A$	---	2.5	3.5	
		$V_{GS}=2.5V$, $I_D=3A$	---	5	7	
		$V_{GS}=1.8V$, $I_D=3A$	---	9	10	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	0.4	---	1.0	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=16V$, $V_{GS}=0V$, $T_J=25\text{ }^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=16V$, $V_{GS}=0V$, $T_J=55\text{ }^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 8V$, $V_{DS}=0V$	---	---	± 10	μA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=3A$	---	42	---	S
Q_g	Total Gate Charge (4.5V)	$V_{DS}=10V$, $I_D=3A$	---	38	---	nC
	Total Gate Charge (3.9V)		---	33	---	
Q_{gs}	Gate-Source Charge		---	4.5	---	
Q_{gd}	Gate-Drain Charge		---	12	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=16V$, $V_{GS}=4.5V$, $R_G=6\Omega$, $I_D=3A$	---	22	---	ns
T_r	Rise Time		---	41	---	
$T_{d(off)}$	Turn-Off Delay Time		---	77	---	
T_f	Fall Time		---	21	---	
C_{iss}	Input Capacitance	$V_{DS}=10V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1200	---	pF
C_{oss}	Output Capacitance		---	193	---	
C_{rss}	Reverse Transfer Capacitance		---	185	---	
I_S	Continuous Source Current ¹	$V_G=V_D=0V$, Force Current	---	---	30	A
I_{SM}	Pulsed Source Current ²		---	---	100	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=3A$, $T_J=25\text{ }^{\circ}\text{C}$	---	---	1.2	V

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, $t \leq 10s$.2.The data tested by pulsed , pulse width $\leq 10\mu s$, duty cycle $\leq 1\%$

Typical Characteristics

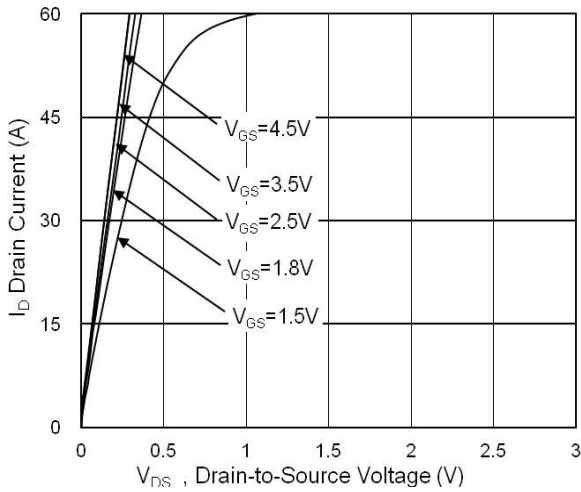


Fig.1 Typical Output Characteristics

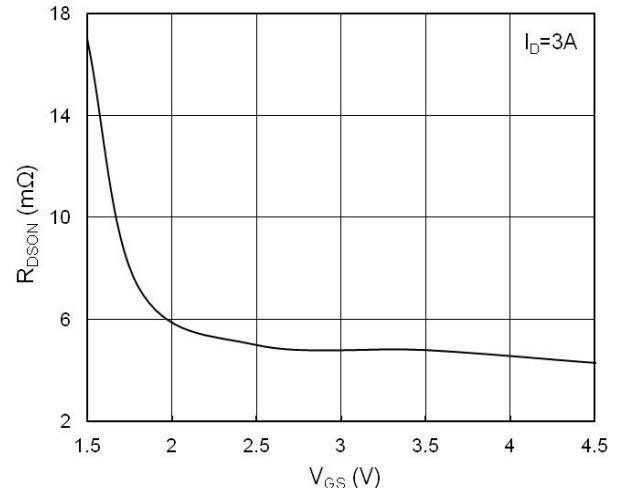


Fig.2 On-Resistance vs. Gate-Source

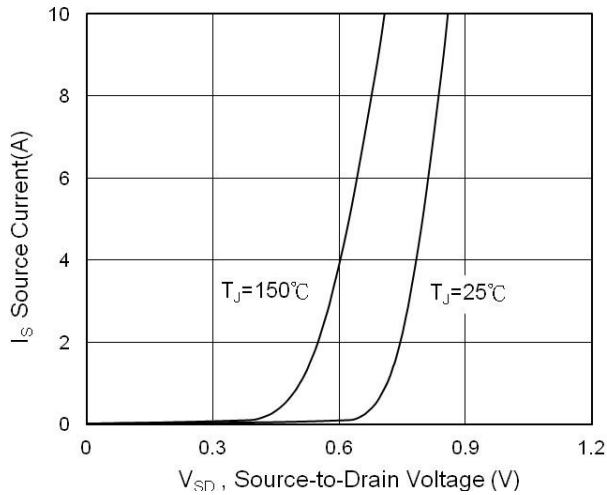


Fig.3 Forward Characteristics Of Reverse

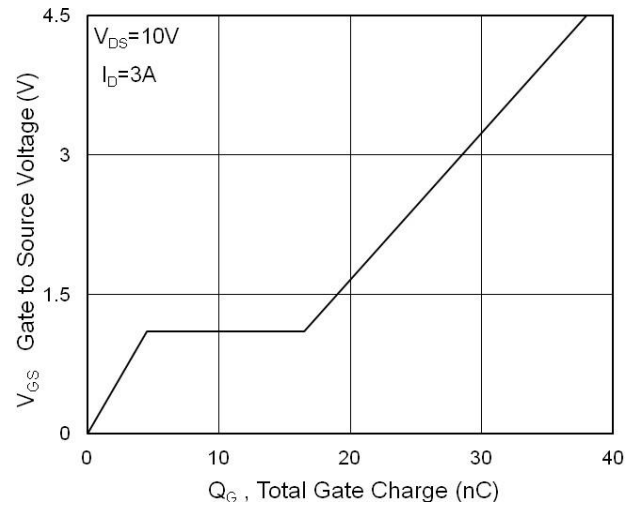


Fig.4 Gate-Charge Characteristics

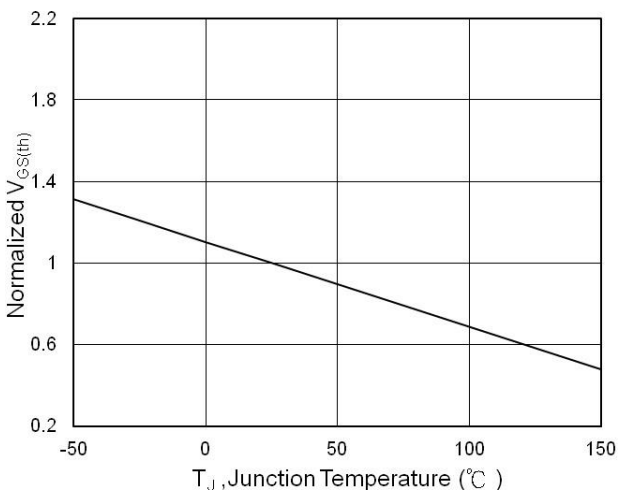


Fig.5 $V_{GS(th)}$ vs. T_J

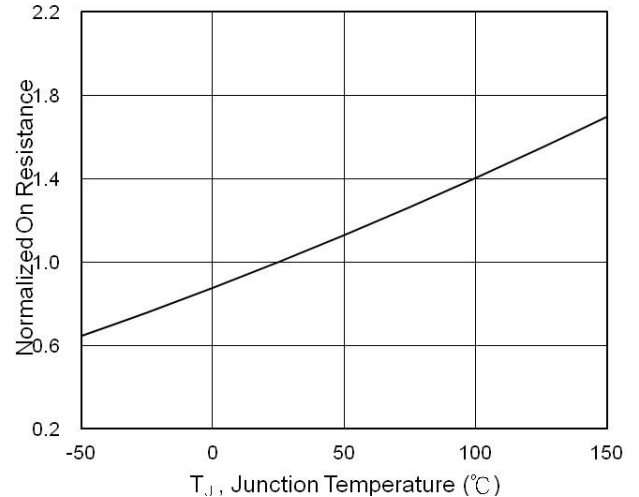


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

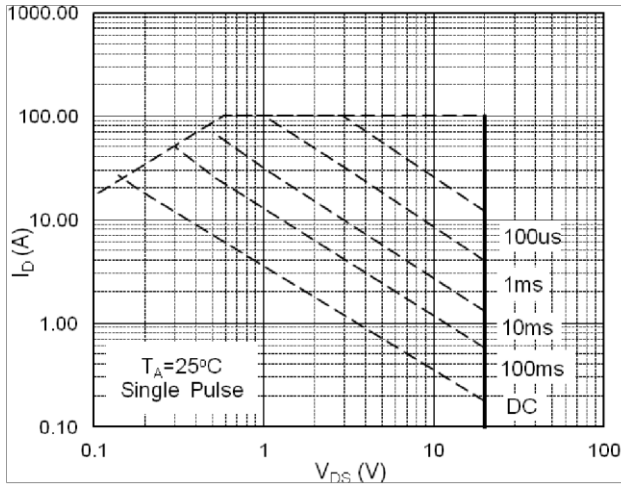


Fig.7 Capacitance

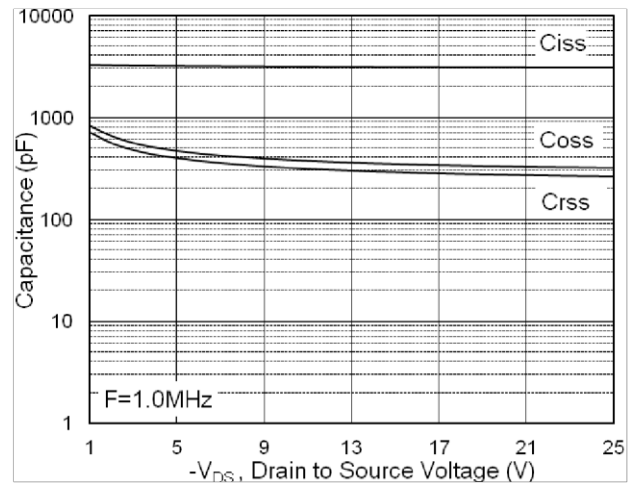


Fig.8 Safe Operating Area

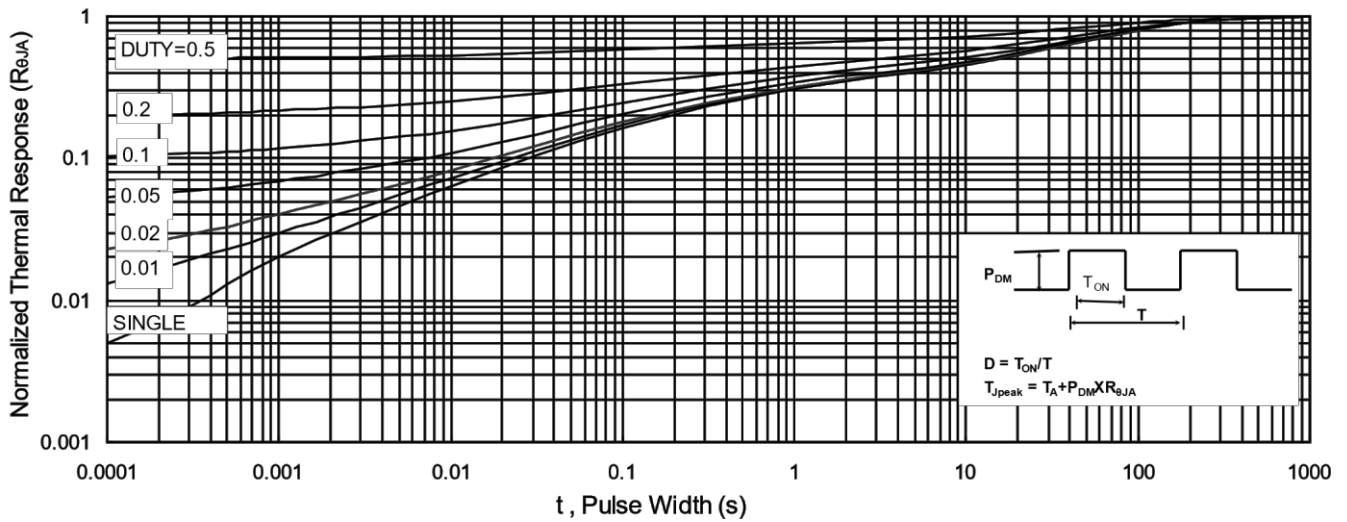


Fig.9 Normalized Maximum Transient Thermal Impedance

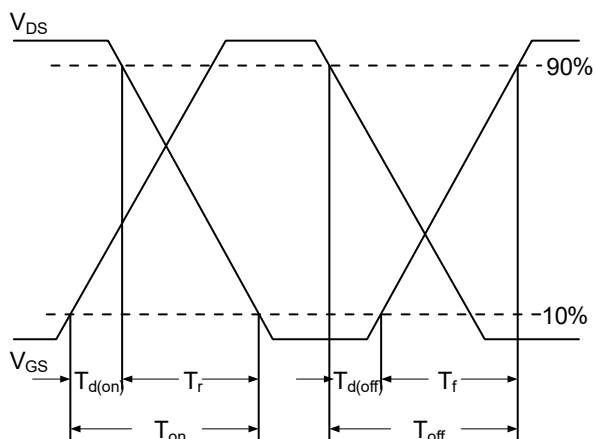


Fig.10 Switching Time Waveform

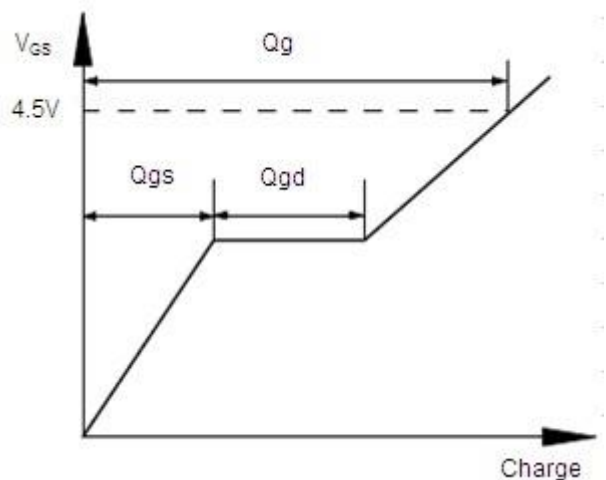
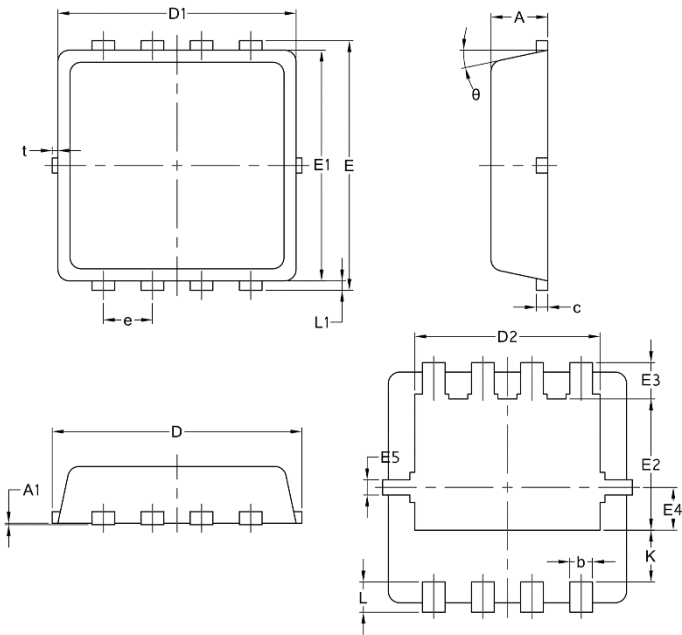


Fig.11 Gate Charge Waveform

Package Mechanical Data-DFN3*3-8L-JQ Single



Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
Φ	10	12	14